Silicon NPN Power Transistors 2SD402

DESCRIPTION

·With TO-220C package
·Complement to type 2SB547
·High breakdown voltage

APPLICATIONS

·Designed for use in line-operated color TV vertical deflection of complementary symmetry circuit

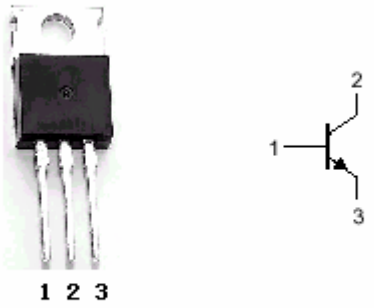


Fig.1 simplified outline (TO-220C) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		2.0	A
I_{CM}	Collector current-Peak		3.0	A
I_B	Base current		1.5	A
P_C	Collector dissipation	T_C=25□	20	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-50~150	□

THERMAL CHARACTERISTICS

SYMBOL	CHARACTERISTICS	MAX	UNIT
Rθjc	Thermal resistance junction to case	4.16	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA; I_B=0	150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=0.5A; I_B=50mA			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=150V; I_E=0			50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=4V; I_C=0			50	μA
h_{FE}	DC current gain	I_C=0.4A ; V_{CE}=10V	40			
f_T	Transition frequency	I_C=0.4A ; V_{CE}=10V		7		MHz
C_C	Collector capacitance	I_E=0 ; V_{CB}=10V;f=1.0MHz		45		pF

PACKAGE OUTLINE

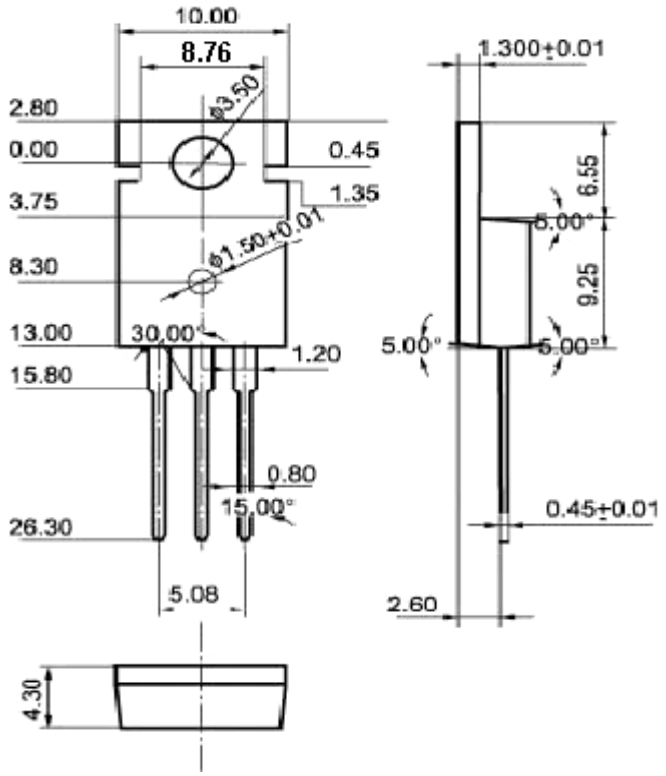


Fig.2 Outline dimensions (unindicated tolerance:±0.10mm)